

Supplementary Materials

Silicon Oxycarbide and Silicon Oxycarbonitride Materials under Concentrated Solar Radiation

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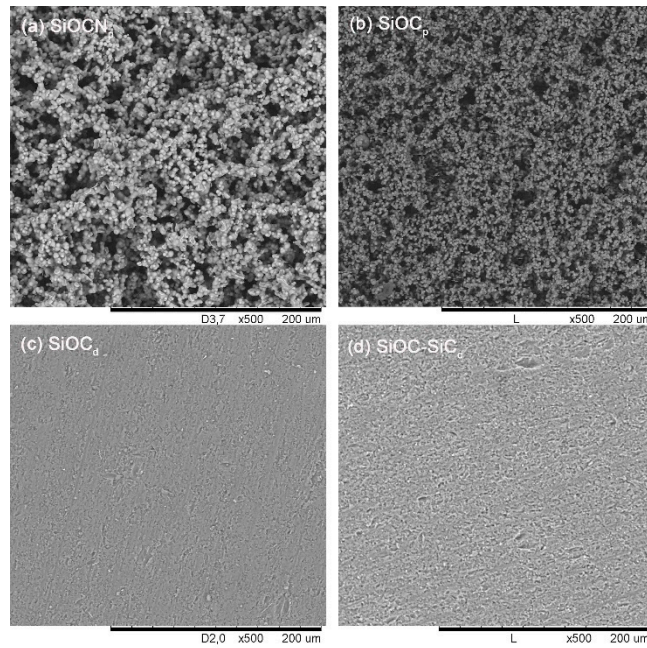


Figure S1. SEM micrographs of the initial surface of (a) SiOCN_p; (b) SiOC_p; (c) SiOC_d; (d) SiOC–SiC_d.

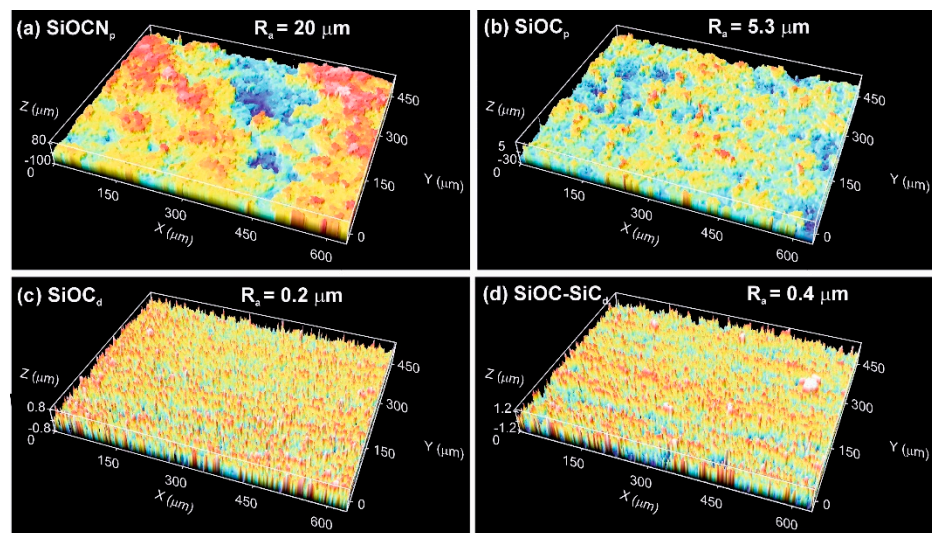


Figure S2. ICM images showing the initial surfaces of samples: (a) SiOCN_p; (b) SiOC_p; (c) SiOC_d; (d) SiOC–SiC_d.

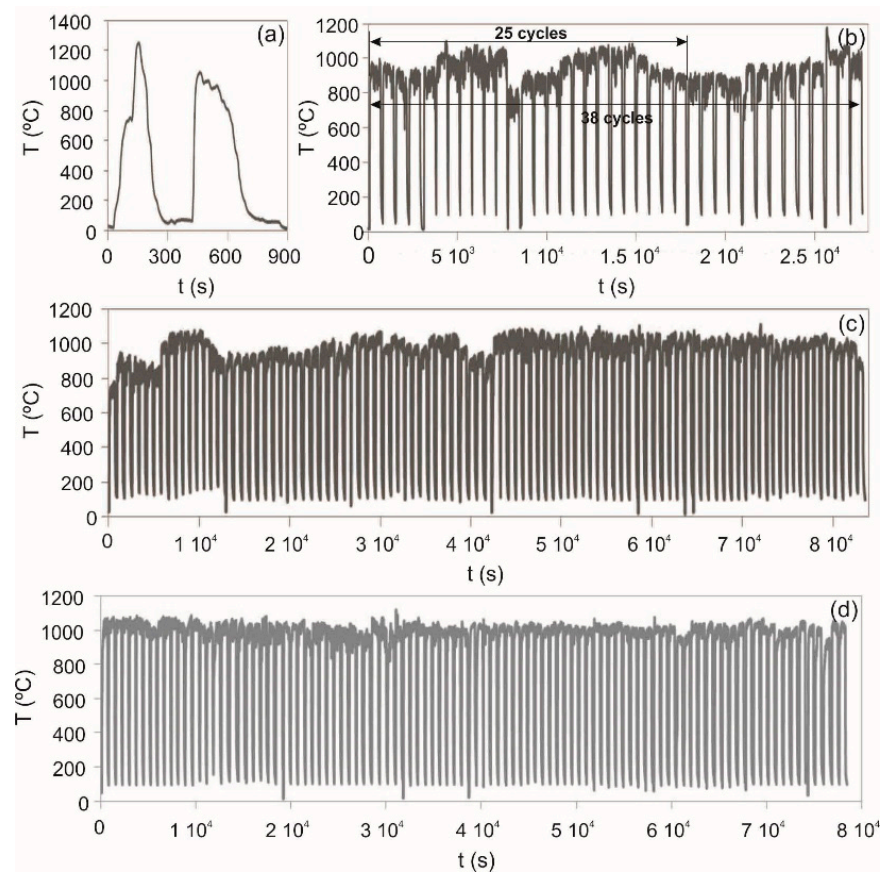


Figure S3. Temperature recordings during the thermal shock tests: (a) SiOCN_p; (b) SiOC_p; (c) SiOC_d; (d) SiOC-SiC_d.

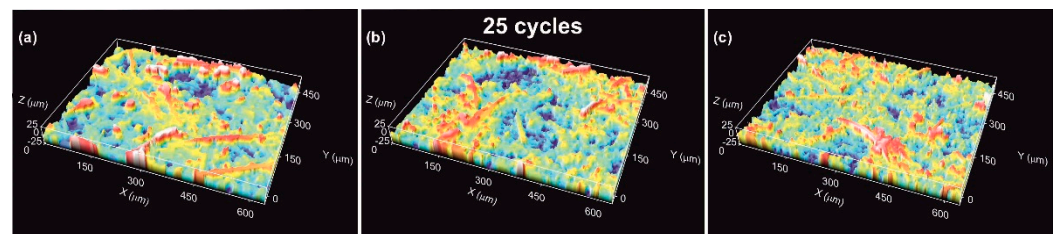


Figure S4. ICM images showing the surface of the SiOC_p sample after 25 cycles of the thermal shock tests: (a) nearest focus area; (b) middle zone; (c) furthest area from the solar radiation focus.